

GD54/74HC643, GD54/74HCT643

OCTAL INVERTING & NONINVERTING 3-STATE TRANSCEIVERS

General Description

These devices are identical in Pinout to the 54/74LS643. They consist of eight transceivers which are designed for Asynchronous two-way communications between Data buses. Each device has 4 inverting and 4 noninverting outputs with Active Low output enable which is used to place the I/O ports into High impedance states.

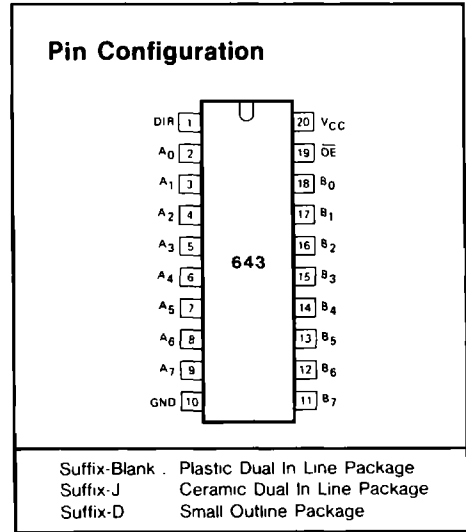
The direction control determines the directions of Data flow. When it is high, Data flow From A to B; When it is low, Data flow from B to A.

Refer to the other devices for similar functionalities;

The HC/HCT245 All noninverting outputs

The HC/HCT640 All inverting outputs.

These devices are characterized for operation over wide temperature ranges to meet industry and military specifications.



Features

- Low Power consumption characteristic of CMOS devices
- Output drive capability: 15 LS TTL Loads Min.
- Operating speed superior to LS TTL
- Wide operating voltage range: for HC 2 to 6 volts
for HCT 4.5 to 5.5 volts
- Low input current: 1 μ A Max.
- Low quiescent current: 80 μ A Max. (74HC)
- High noise immunity characteristic of CMOS
- Diode protection on all inputs

Function Table

INPUTS		INPUTS/OUTPUTS	
\overline{OE}	DIR	A_n	B_n
L	L	A=B	inputs
L	H	inputs	$B = \overline{A}$
H	X	Z	Z

H = HIGH voltage level
 L = LOW voltage level
 X = don't care
 Z = high impedance OFF-state

Absolute Maximum Ratings

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX	UNIT
V_{CC}	DC Supply voltage		-0.5	+7	V
I_{iP}, I_{oK}	DC input or output diode current	for $V_i < -0.5$ or $V_i > V_{CC} + 0.5V$		20	mA
I_o	DC output source or sink current	for $-0.5V < V_o < V_{CC} + 0.5V$		35	mA
I_{CC}	DC V_{CC} or GND current			70	mA
T_{stj}	Storage temperature range		-65	150	°C
P_D	Power dissipation per package	above +70°C derate linearly with 8mW/K		500	mW
T_L	Lead temperature	At distance 1:16 ± 1:32 in from case for 60 sec(CERAMIC) 10 sec(PLASTIC)		300 260	°C

Recommended Operating Conditions

CHARACTERISTIC	LIMITS		UNITS
	MIN	MAX	
Supply-Voltage Range V_{CC} GD54 74HC Types GD54 74HCT Types	2 4.5	6 5.5	V
DC Input or Output Voltage V_i, V_o	0	V_{CC}	V
Operating Temperature T_A GD74 Types GD54 Types	-40 -55	+85 +125	°C
Input Rise and Fall times t_r, t_f GD54 74HC Types at 2V at 4.5V at 6V GD54 74HCT Types at 4.5V		1000 500 400 500	ns

Logic Diagram

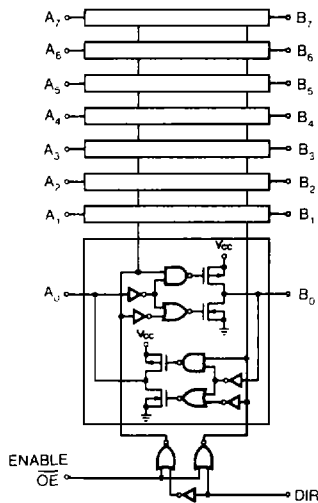


Fig. 1 Logic diagram

DC Electrical Characteristics for HC

SYMBOL	PARAMETER	TEST CONDITION	V _{CC} (V)	T _A =25°C			GD74HC643		GD54HC643		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.		
V _{IH}	HIGH level input Voltage		2.0 4.5 6.0	1.5 3.15 4.2			1.5 3.15 4.2		1.5 3.15 4.2		V	
V _{IL}	LOW level input voltage		2.0 4.5 6.0			0.3 0.9 1.2		0.3 0.9 1.2		0.3 0.9 1.2	V	
V _{OH}	HIGH level output voltage	V _{IN} =V _{IH} or V _{IL}	I _{OH} =-20μA	2.0	1.9	2.0		1.9		1.9		V
				4.5	4.4	4.5		4.4		4.4		
				6.0	5.9	6.0		5.9		5.9		
V _{OL}	LOW level output voltage	V _{IN} =V _{IH} or V _{IL}	I _{OL} =20μA	2.0			0.1		0.1		0.1	V
				4.5			0.1		0.1		0.1	
				6.0			0.1		0.1		0.1	
V _{OL}	LOW level output voltage	V _{IN} =V _{IH} or V _{IL}	I _{OL} =6mA	4.5		0.17	0.26		0.33		0.4	V
				6.0		0.15	0.26		0.33		0.4	
				6.0					0.33		0.4	
I _{IN}	Input leakage Current	V _{IN} =V _{CC} or GND	6.0			0.1		1.0		1.0	μA	
I _{OZ}	Three-State leakage current	V _{IN} =V _{IH} or V _{IL} V _O =V _{CC} or GND	6.0		0.01	0.5		5.0		10.0	μA	
I _{CC}	Quiescent Supply Current	V _{IN} =V _{CC} or GND I _{out} =0μA	6.0			8		80		160	μA	

DC Electrical Characteristics for HCT

SYMBOL	PARAMETER	TEST CONDITION	V _{CC} (V)	T _A =25°C			GD74HCT643		GD54HCT643		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.		
V _{IH}	HIGH level input Voltage		4.5 to 5.0	2.0			2.0		2.0		V	
V _{IL}	LOW level input voltage		4.5 to 5.5			0.8		0.8		0.8	V	
V _{OH}	HIGH level output voltage	V _{IN} =V _{IH} or V _{IL}	I _{OH} =-20μA	4.5	4.4	4.5		4.4		4.4		V
			I _{OH} =-6mA	4.5	3.98	4.3		3.84		3.7		
V _{OL}	LOW level output voltage	V _{IN} =V _{IH} or V _{IL}	I _{OL} =20μA	4.5			0.1		0.1		0.1	V
			I _{OL} =6mA	4.5		0.17	0.26		0.33		0.4	
I _{IN}	Input leakage Current	V _{IN} =V _{CC} or GND	5.5			0.1		1.0		1.0	μA	
I _{OZ}	Three-State leakage current	V _{IN} =V _{IH} or V _{IL} V _O =V _{CC} or GND	5.5		0.01	0.5		5.0		10.0	μA	
I _{CC}	Quiescent Supply Current	V _{IN} =V _{CC} or GND I _{out} =0μA	5.5			8		80		160	μA	

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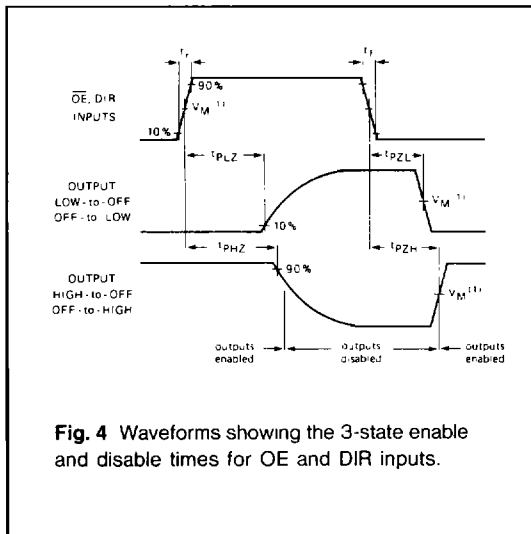
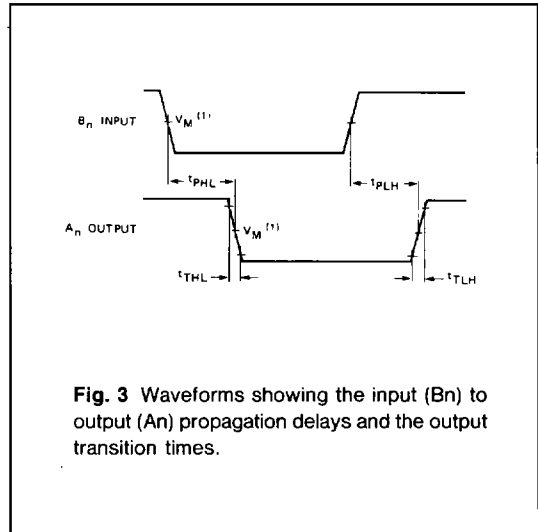
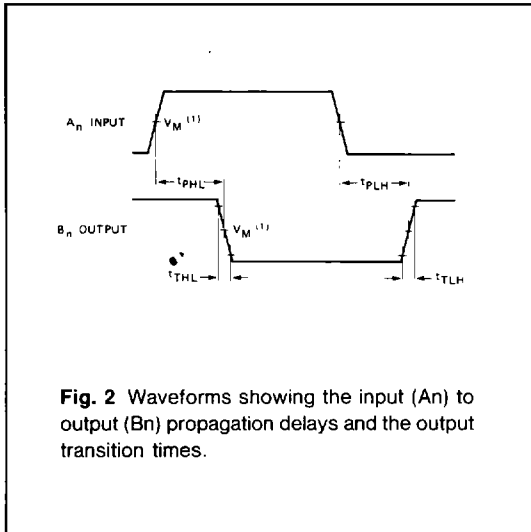
AC Characteristics for HC: $t_r=t_f=6ns$ $C_L=50$ pF

SYMBOL	PARAMETER	V _{CC} (V)	T _A =25°C			GD74HC643		GD54HC643		UNIT
			MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.	
t _{PLH} / t _{PHL}	Propagation Delay Time An to Bn; Inverting	2.0		300	100		120		140	ns
		4.5		10	20		25		30	
		6.0		9	18		22		26	
t _{PLH} ' t _{PHL}	Propagation Delay Time Bn to An; Non-Inverting	2.0		34	110		130		160	ns
		4.5		12	22		28		32	
		6.0		11	20		24		28	
t _{PZH} ' t _{PZL}	3-state Output Enable Time \overline{OE} , DIR to An; \overline{OE} , DIR to Bn	2.0		45	140		180		210	ns
		4.5		18	30		38		45	
		6.0		16	26		32		38	
t _{PLZ} ' t _{PHZ}	3-State Output Disable Time \overline{OE} , DIR to An; \overline{OE} , DIR to Bn	2.0		45	140		180		210	ns
		4.5		18	30		38		45	
		6.0		16	26		32		38	
t _{TLH} ' t _{THL}	Output Transition Time	2.0		15	60		75		90	ns
		4.5		6	12		15		18	
		6.0		5	10		13		15	

AC Characteristics for HCT: $t_r=t_f=6ns$ $C_L=50$ pF

SYMBOL	PARAMETER	V _{CC} (V)	T _A =25°C			GD74HCT643		GD54HCT643		UNIT
			MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.	
t _{PLH} / t _{PHL}	Propagation Delay Time An to Bn; Inverting	4.5		13	26		28		32	ns
t _{PLH} ' t _{PHL}	Propagation Delay Time Bn to An; Non-Inverting	4.5		15	28		32		38	ns
t _{PZH} ' t _{PZL}	3-state Output Enable Time \overline{OE} , DIR to An; \overline{OE} , DIR to Bn	4.5		19	35		45		52	ns
t _{PLZ} ' t _{PHZ}	3-State Output Disable Time \overline{OE} , DIR to An; \overline{OE} , DIR to Bn	4.5		19	35		45		52	ns
t _{TLH} ' t _{THL}	Output Transition 1 me	4.5		7	12		15		18	ns

AC Waveforms



Note to AC waveforms

(1) HC $V_M = 50\%$ $V_I = \text{GND to } V_{CC}$
 HCT $V_M = 1.3V$ $V_I = \text{GND to } 3V$